

REMARKS

Claims 1-81 are cancelled, and new claims 82-97 are added. Claims 82-97 are pending in the application.

The previously-pending claims were rejected over Paek in view of Nakamura. The new claims 82-97 are believed allowable over the cited references.

Referring initially to new claim 82, such recites a method of forming a low electrical resistance metal silicide. Specifically, the claim recites that a first metal silicide is formed over a substrate, a metal-containing layer is formed against the first metal silicide layer, and a silicon-containing layer is formed directly against the metal-containing layer and on an opposing side of the metal-containing layer from the first metal silicide layer. The claim further recites that metal of the metal-containing layer is converted to metal silicide to convert the metal-containing layer to a second metal silicide layer, and that such conversion incorporates silicon from the silicon-containing layer into the second metal silicide layer. Finally, the claim recites that the first metal silicide layer, second metal silicide layer, and silicon-containing layer are patterned into a line having substantially vertical sidewalls extending across the first metal silicide layer, second metal silicide layer and silicon-containing layer.

New claim 82 is supported by the originally-filed application at, for example, Figs. 1-4, where a line is shown to be patterned from a first metal silicide layer 18, second metal silicide layer 26, and silicon-containing layer 22. Accordingly, claim 82 does not comprise

"new matter". It is noted that claim 82 is also supported by Figs. 7-9 where a line is shown to be patterned from a first metal silicide layer 110, second metal silicide layer 120, and a silicon-containing 114.

Claim 82 is allowable over the cited references for at least the reason that the references do not suggest or disclose the recited formation of the first metal silicide layer, second metal silicide layer, and silicon-containing layer, together with the patterning of such first metal silicide layer, second metal silicide layer, and a silicon-containing layer into a line having substantially vertical sidewalls extending across the first metal silicide layer, second metal silicide layer, and silicon-containing layer.

Claims 83-87 depend from claim 82, and are therefore allowable over the cited references for at least the reasons discussed above regarding claim 82.

Referring next to independent claims 88 and 91, such claims, like the above-discussed claim 82, recite methods in which a first metal silicide layer, second metal silicide layer and silicon-containing layer are formed, and then patterned into a line having substantially vertical sidewalls extending across the first metal silicide layer, second metal silicide layer, and silicon-containing layer. Claims 88 and 91 are therefore allowable for reasons similar to those discussed above regarding claim 82.

Claims 89, 90 and 92-97 depend from claims 88 and 91, and are therefore allowable for at least the reasons for which independent claims 88 and 91 are allowable.

New claims 82-97 are believed allowable over the cited references. Applicant therefore respectfully requests that the Examiner's next action be a Notice of Allowance formally allowing the new claims.

Dated: _____

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Respectfully submitted,

By: _____



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